

# INTERNATIONAL STANDARD

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**Semiconductor devices - Mechanical and climatic test methods -  
Part 23: High temperature operating life**

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This edition includes the following significant technical changes with respect to the previous edition:

- a) absolute stress test definitions and resultant test durations have been updated.

## **1 Scope**

This part of IEC 60749 specifies the test used to determine the effects of bias conditions and temperature on solid state devices over time. It simulates the device operating condition in an accelerated way and is primarily for device qualification and reliability monitoring. A form of high temperature bias life using a short duration, popularly known as "burn-in", can be used to screen for infant-mortality related failures. The detailed use and application of burn-in is outside the scope of this document.

## **2 Normative references**

There are no normative references in this document.

## Bibliography

IEC 60747 (all parts), *Semiconductor devices - Discrete devices and integrated circuits*

IEC 60749-34, *Semiconductor devices - Mechanical and climatic test methods - Part 34: Power cycling*

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